

DESCRIPTION

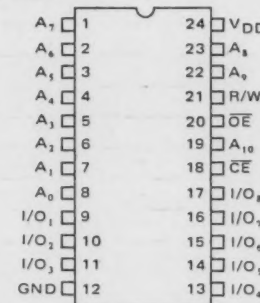
The TC5517AP/AF in a 16384-bit static random access memory organized as 2048 words by 8 bits using CMOS technology, and operates from a single 5 volt supply.

The TC5517AP/AF is featured by output enable and chip enable inputs, that is, \overline{OE} for fast memory access and \overline{CE} for a minimum standby current mode, and is suited for low power application where battery operation or battery back up for nonvolatility are required. Furthermore the TC5517APL guaranteed a

FEATURES

- Standby Current
 - 0.2 μ A (Max.) at $T_a = 25^\circ\text{C}$ } TC5517APL/AFL
 - 1.0 μ A (Max.) at $T_a = 60^\circ\text{C}$ }
 - 1.0 μ A (Max.) at $T_a = 25^\circ\text{C}$ } TC5517AP/AF
 - 5.0 μ A (Max.) at $T_a = 60^\circ\text{C}$ }
- Low Power Dissipation : 200mW (Typ.) operating
- Single 5V Power Supply : $5V \pm 10\%$
- Data Retention Supply Voltage: 2.0 ~ 5.5V
- Fully Static Operation

PIN CONNECTION (TOP VIEW)



PIN NAMES

$A_0 \sim A_{10}$	Address Inputs
R/W	Read/Write Control Input
\overline{OE}	Output Enable Input
\overline{CE}	Chip Enable Input
$I/O_1 \sim I/O_8$	Data Input/Output
V_{DD}	Power (+5V)
GND	Ground

standby current equal to or less than 1 μ A at 60°C ambient temperature is available.

The TC5517AP is also featured by pin compatibility with 2716 type EPROM. This means that the TC5517AP and EPROM can be interchanged in the same socket, and the flexibility in the definition of the quantity of RAM versus EPROM obtained as a result allows the wide application in microcomputer system.

- Access Time
 - 250ns (Max.) : TC5517AP/APL/AF/AFL
 - 200ns (Max.) : TC5517AP-2/APL-2/AF-2/AFL-2
- Two Control Input (\overline{CE} , \overline{OE})
- Pin Compatible with Nch Static RAM TMM2016P
- All Inputs and Outputs Directly TTL Compatible
- Three State Outputs
- Package
 - Plastic DIP : TC5517AP/APL
 - Plastic FP : TC5517AF/AFL

BLOCK DIAGRAM

